

Lead (Pb) Free Product RoHS compliant

SMC830

High Performance infrared SMD LED on ceramics

SMC830 consists of an AlGaAs LED mounted on the ceramics package and is sealed with silicone or epoxy resin. It emits a spectral band of radiation at 830nm.

◆ Specifications

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|---------------------|-------------------------|
| 1) Product Name | SMD type infrared LED |
| 2) Type No. | SMC830 |
| 3) Chip | |
| (1) Chip Material | AlGaAs |
| (2) Peak Wavelength | 830nm typ. |
| 4) Package | |
| (1) Package | Ceramics |
| (2) Lens | Silicone or Epoxy resin |

◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P _D	190	mW	T _a =25°C
Forward Current	I _F	100	mA	T _a =25°C
Pulse Forward Current	I _{FP}	500	mA	T _a =25°C
Reverse Voltage	V _R	5	V	T _a =25°C
Operating Temperature	T _{OPR}	-20 ~ +80	°C	
Storage Temperature	T _{STG}	-30 ~ +80	°C	
Soldering Temperature	T _{SOL}	240	°C	

‡Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

‡Soldering condition: Soldering condition must be completed within 3 seconds at 240°C

◆ Electro-Optical Characteristics [T_a=25°C]

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F =50mA		1.60	1.80	V
Reverse Current	I _R	V _R =5V			10	uA
Total Radiated Power	P _O	I _F =50mA	5.0	10.0		mW
Radiant Intensity	I _E	I _F =50mA	3.0	5.0		mW/sr
Peak Wavelength	λ _P	I _F =50mA		830		nm
Half Width	Δλ	I _F =50mA		35		nm
Viewing Half Angle	θ _{1/2}	I _F =50mA		±55		deg.
Rise Time	t _r	I _F =50mA		60		ns
Fall Time	t _f	I _F =50mA		40		ns

‡Total Radiated Power is measured by Photodyne #500

‡Radiant Intensity is measured by Tektronix J-6512.

◆ Outer dimension (Unit : mm)

